2T360 – low power PNP transistor

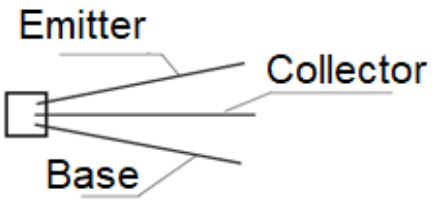
Features

Typical Ft = 550 MHz
P_{Cmax}= 10 mW
U_{CEmax}=20 V(2T360A); 15V (2T360B, 2T360V)

Silicon epitaxial PNP bipolar transistors 2T360A, 2T360B, 2T360V are intendent to use in general purpose applications, industrial automation .

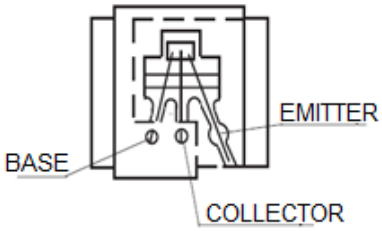
Suffix "-1" if packaged in TC-1. For example : 2T360A-1 , 2T360B-1 , 2T360V-1

Pinout

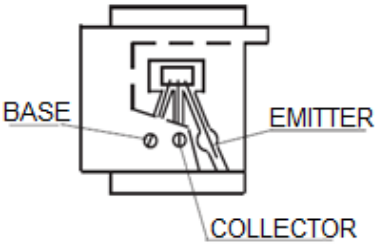


2T360A, 2T360B, 2T360V

Packaging



TC1



TC1B

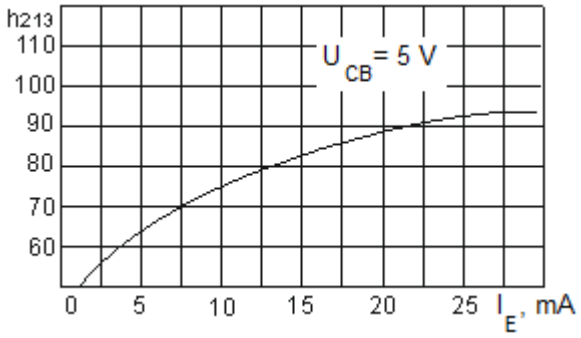
Electrical parameters (T = 25±10 °C)

Parameter	Parameter name	2T360A		2T360B		2T360V	
		min	max	min	max	min	max
Reverse collector current , uA (U_{CB}=25V for 2T360A; U_{CB}=20V for 2T360B, 2T360V)	I_{CBO}		1		1		1
Reverse emitter current , uA (U_{EB}=5 V 2T360A ; U_{EB}=4 V 2T360B, 2T360V)	I_{EBO}		0,5		0,5		0,5
Static current transfer (U_{CB}= 1V, I_E= 10 mA , t_{imp} < 2 ms)	$h_{21Э}$	25	70	40	120	80	240
High frequency current transfer (U_{CB}=2 V, I_E= 5 mA , f =100 MHz)	$\lvert h_{21E} \rvert$	3		4		4	
Collector-emitter saturation , V (I_C=10 mA , I_B= 1 mA)	U_{CEsat}		0,35		0,35		0,35
Base-emitter saturation (I_c=10 mA, I_B=1 mA), V	U_{BEsat}		1,2		1,2		1,2
Feedback loop time constant at high frequency (U_{CB}=2 V, I_E=5 mA, f=5 MHz)	τ_k		450		450		450
Collector capacitance (U_{CB} = 5 V, f = 10 MHz), pF	C_C		5		5		5
Emitter capacitance (U_{EB}= 0 V , f = 10 MHz), pF	C_E		7		7		7

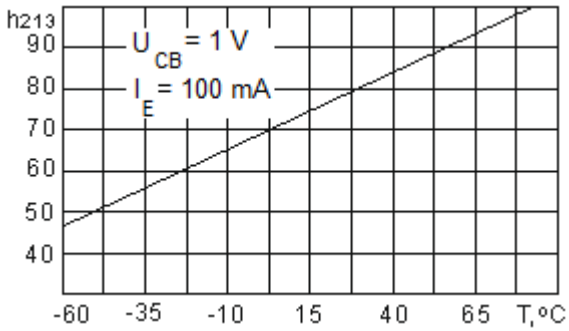
Maximum electrical parameters

Parameter	Parameter name	2T360A	2T360B	2T360V
Maximum collector – base voltage , V	U_{CBmax}	25	20	20
Maximum collector-emitter voltage , R_{BE}≤10 kOhm, V	U_{CEmax}	20	15	15
Maximum emitter-base voltage , V	U_{BEmax}	5	4	4
Maximum collector current , mA	I_{Cmax}	20	20	20
Impulse collector current t_{imp} ≤ 1 usec, Q ≥ 10, mA	$I_{CImpmax}$	75	75	75
Dissipated collector power , mW Tamb=+55°C Tamb=+85°C	P_{Cmax}	 10 5	 10 5	 10 5
Thermal resistance , °C/mW	$R_{T\ п-с}$	7	7	7

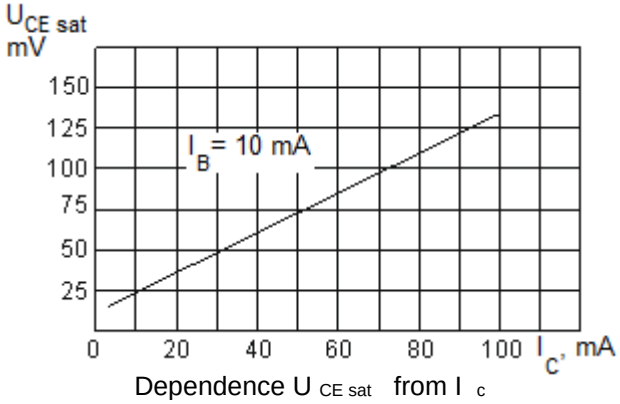
General typical parameters



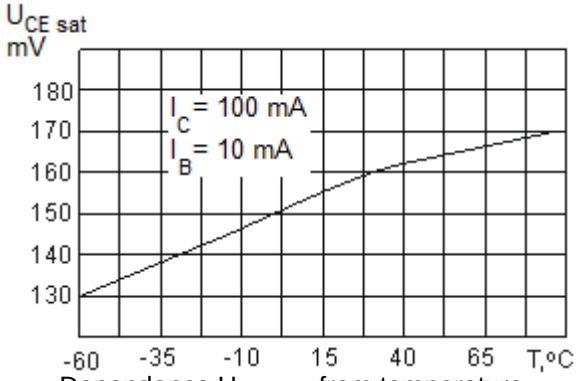
Dependence $H21_E$ from I_E



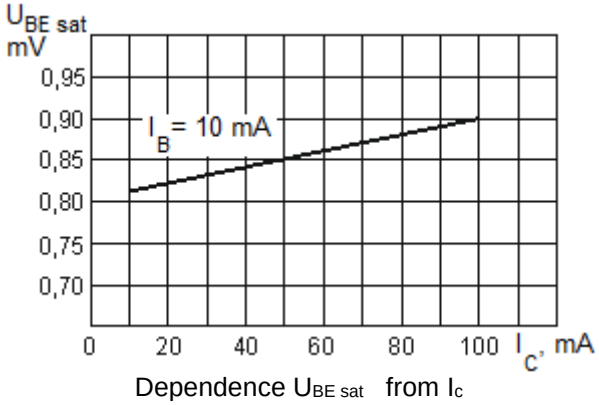
Dependence $H21_E$ from temperature



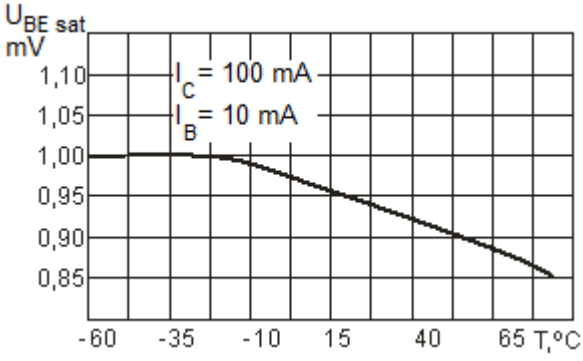
Dependence $U_{CE\ sat}$ from I_c



Dependence $U_{CE\ sat}$ from temperature



Dependence $U_{BE\ sat}$ from I_c



Dependence $U_{BE\ sat}$ from temperature